

Interfacial Carrier Transport Property of Gallium Nitride Epilayer/Quantum Dot Hybrid Structure

Huiyun Wei^{a,c,d}, Peng Qiu^a, Meina Yu^b, Yimeng Song^a, Ye Li^a, Yingfeng He^a,

Mingzeng Peng^a, Xiaohu Liu^{c,d*}, and Xinhe Zheng^{a*}

^a*Beijing Advanced Innovation Center for Materials Genome Engineering, Beijing Key Laboratory for Magneto-Photoelectrical Composite and Interface Science, School of Mathematics and Physics, University of Science and Technology Beijing, Beijing, 100083, PR China*

^b*University of Science and Technology Beijing, Beijing, 100083, PR China*

^c*School of Biomedical Engineering, School of Ophthalmology & Optometry, Wenzhou Medical University, Wenzhou 325027, PR China.*

^d*Engineering Research Center of Clinical Functional Materials and Diagnosis & Treatment Devices of Zhejiang Province, Wenzhou Institute, University of Chinese Academy of Sciences (Wenzhou Institute of Biomaterials & Engineering), Wenzhou 325027, PR China.*

*Correspondence: liuxiaohu@wmu.edu.cn; xinhezhenh@ustb.edu.cn;

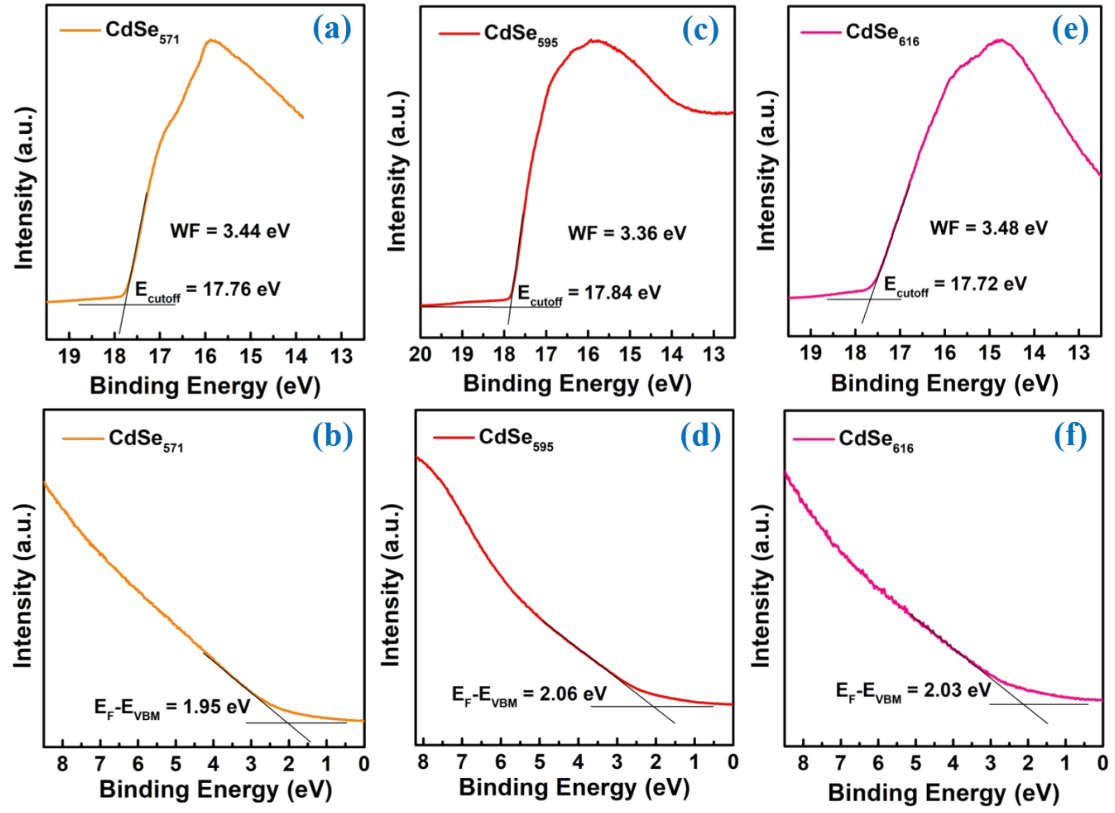


Figure S1. UPS spectra of the CdSe_{571} QDs, CdSe_{595} QDs and CdSe_{616} QDs.